TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74VCX162373FT

Low-Voltage 16-Bit D-Type Latch with 3.6-V Tolerant Inputs and Outputs

The TC74VCX162373FT is a high-performance CMOS 16-bit D-type latch. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

This 16-bit D-type latch is controlled by a latch enable input (LE) and an output enable input  $(\overline{OE})$  which are common to each byte. It can be used as two 8-bit latches or one 16-bit latch. When the  $\overline{OE}$  input is high, the outputs are in a high-impedance state.

The 26- $\Omega$  series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

## Features

- $26-\Omega$  series resistors on outputs
- Low-voltage operation:  $V_{CC} = 1.8$  to 3.6 V

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• High-speed operation:  $t_{pd} = 3.3 \text{ ns} (max) (V_{CC} = 3.0 \text{ to } 3.6 \text{ V})$ 

$$t_{pd}$$
 = 4.5 ns (max) (V<sub>CC</sub> = 2.3 to 2.7 V)

$$t_{pd} = 5.8 \text{ ns} (max) (V_{CC} = 1.8 \text{ V})$$

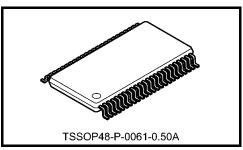
- Output current:  $I_{OH}/I_{OL} = \pm 12 \text{ mA} \text{ (min)} (V_{CC} = 3.0 \text{ V})$ 
  - $: I_{OH}/I_{OL} = \pm 8 \text{ mA} (min) (V_{CC} = 2.3 \text{ V})$

$$I_{OH}/I_{OL} = \pm 4 \text{ mA (min)} (V_{CC} = 1.8 \text{ V})$$

- Latch-up performance: -300 mA
- ESD performance: Machine model  $\geq \pm 200 \text{ V}$

Human body model  $\geq \pm 2000 \text{ V}$ 

- Package: TSSOP
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs



Weight: 0.25 g (typ.)

# Pin Assignment (top view)

			1	
10E	1	$\bigcirc$	48	1LE
1Q1	2		47	1D1
1Q2	3		46	1D2
GND	4		45	GND
1Q3	5		44	1D3
1Q4	6		43	1D4
V <sub>CC</sub>	7		42	V <sub>CC</sub>
1Q5	8		41	1D5
1Q6	9		40	1D6
GND	10		39	GND
1Q7	11		38	1D7
1Q8	12		37	1D8
2Q1	13		36	2D1
2Q2	14		35	2D2
GND	15		34	GND
2Q3	16		33	2D3
2Q4	17		32	2D4
V <sub>CC</sub>	18		31	V <sub>CC</sub>
2Q5	19		30	2D5
2Q6	20		29	2D6
GND	21		28	GND
2Q7	22		27	2D7
2Q8	23		26	2D8
$2\overline{OE}$	24		25	2LE
		L	1	

# IEC Logic Symbol

105	1 🕟	1EN			
	48				
1LE —	24	C3			
20E —	25	2EN			
2LE —	25	C4			
1D1 —	47	3D	1 🗸	2	1Q1
1D2 —	46			3	1Q2
1D3 —	44			5	1Q3
1D4 —	43			6	1Q4
1D5 —	41			8	1Q5
1D6 —	40			9	1Q6
1D7 —	38			11	1Q7
1D7 1D8 —	37			12	1Q8
2D1 —	36	4D	2 🗸	13	2Q1
2D1 2D2 —	35	40	2 V	14	2Q1
	33			16	
2D3 —	32			17	2Q3
2D4 —	30			19	2Q4
2D5 —	29			20	2Q5
2D6 —	27			20	2Q6
2D7 —	26			23	2Q7
2D8 —	20			20	2Q8

# <u>TOSHIBA</u>

#### **Truth Table**

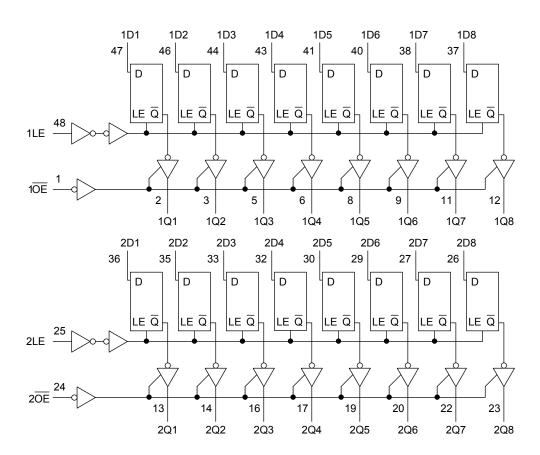
	Outputs		
1 <del>0E</del>	1LE	1D1-1D8	1Q1-1Q8
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

	Outputs		
20E	2LE	2D1-2D8	2Q1-2Q8
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	н	Н

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

## System Diagram



#### Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Symbol Rating		
Power supply voltage	V <sub>CC</sub>	-0.5 to 4.6	V	
DC input voltage	V <sub>IN</sub>	-0.5 to 4.6	V	
		-0.5 to 4.6 (Note 2)		
DC output voltage	VOUT	–0.5 to V <sub>CC</sub> + 0.5	V	
		(Note 3)		
Input diode current	lık	-50	mA	
Output diode current	I <sub>OK</sub>	±50 (Note 4)	mA	
DC output current	lout	±50	mA	
Power dissipation	PD	400	mW	
DC $V_{CC}$ /ground current per supply pin	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA	
Storage temperature	T <sub>stg</sub>	–65 to 150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 2: OFF state
- Note 3: High or low state. IOUT absolute maximum rating must be observed.
- Note 4:  $V_{OUT} < GND, V_{OUT} > V_{CC}$

#### **Operating Ranges (Note 1)**

Characteristics	Characteristics Symbol Rating		Unit
Power supply voltage	V <sub>CC</sub>	1.8 to 3.6	V
Tower supply voltage	VCC	1.2 to 3.6 (Note 2)	v
Input voltage	V <sub>IN</sub>	-0.3 to 3.6	V
Output voltage	Vout	0 to 3.6 (Note 3)	V
Oulput voltage	V001	0 to V <sub>CC</sub> (Note 4)	v
		±12 (Note 5)	
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

- Note 3: OFF state
- Note 4: High or low state
- Note 5:  $V_{CC} = 3.0$  to 3.6 V
- Note 6:  $V_{CC} = 2.3$  to 2.7 V
- Note 7:  $V_{CC} = 1.8 V$
- Note 8:  $V_{IN} = 0.8$  to 2.0 V,  $V_{CC} = 3.0$  V

Note 2: Data retention only

## **Electrical Characteristics**

#### DC Characteristics (Ta = -40 to 85°C, 2.7 V < V<sub>CC</sub> $\leq$ 3.6 V)

Characteristics		Symbol	Test		Min	Max	Unit	
		Symbol			V <sub>CC</sub> (V)			IVIIII
	H-level	VIH		_	2.7 to 3.6	2.0	_	V
Input voltage	L-level	VIL		_	2.7 to 3.6	_	0.8	v
				I <sub>OH</sub> = -100 μA	2.7 to 3.6	V <sub>CC</sub> - 0.2	_	
	H-level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -6 mA	2.7	2.2	_	
				I <sub>OH</sub> = -8 mA	3.0	2.4	_	
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2	_	V
		L-level V <sub>OL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 100 μA	2.7 to 3.6	_	0.2	
				I <sub>OL</sub> = 6 mA	2.7	_	0.4	
	L-level			I <sub>OL</sub> = 8 mA	3.0	_	0.55	
				$I_{OL} = 12 \text{ mA}$	3.0	_	0.8	
Input leakage curr	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μA
3-state output OFF state current		I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		2.7 to 3.6	_	±10.0	μA
Power-off leakage	current	IOFF	$V_{IN}$ , $V_{OUT} = 0$ to 3.6 V	V	0		10.0	μA
Qui a cata a			$V_{IN} = V_{CC}$ or GND		2.7 to 3.6		20.0	
Quiescent supply	current	Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		2.7 to 3.6		±20.0	μA
Increase in I <sub>CC</sub> pe	r input	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6		750	

## DC Characteristics (Ta = -40 to 85°C, 2.3 V $\leq$ V<sub>CC</sub> $\leq$ 2.7 V)

Character	istics	Symbol	Test C	Test Condition		Min	Max	Unit
Input voltage	H-level	VIH	-	_	2.3 to 2.7	1.6	_	V
Input voltage	L-level	VIL	-		2.3 to 2.7	_	0.7	v
				I <sub>OH</sub> = -100 μA	2.3 to 2.7	V <sub>CC</sub> - 0.2	_	
	H-level	Vон	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -4 \text{ mA}$	2.3	2.0		
				$I_{OH} = -6 \text{ mA}$	2.3	1.8		V
Output voltage				$I_{OH} = -8 \text{ mA}$	2.3	1.7		
		V <sub>OL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 100 μA	2.3 to 2.7	_	0.2	
	L-level			$I_{OL} = 6 \text{ mA}$	2.3	_	0.4	
				$I_{OL} = 8 \text{ mA}$	2.3	_	0.6	
Input leakage curre	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μA
2 state sutput OEE	atata aurrant	1	$V_{IN} = V_{IH} \text{ or } V_{IL}$		2.3 to 2.7		±10.0	۸
3-state output OFF	State current	loz	$V_{OUT} = 0$ to 3.6 V		2.3 10 2.7	_	±10.0	μA
Power-off leakage	current	IOFF	$V_{IN}$ , $V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA
Quiescent supply of	urrent		$V_{IN} = V_{CC}$ or GND		2.3 to 2.7	_	20.0	
Quiescent supply t		Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.$	6 V	2.3 to 2.7	_	±20.0	μA

# DC Characteristics (Ta = -40 to 85°C, 1.8 V $\leq$ V<sub>CC</sub> < 2.3 V)

Characteristics Symbol Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit			
Input voltage	H-level	VIH	_	_	1.8 to 2.3	$0.7 \times V_{CC}$	_	V
Input voltage		VIL	_		1.8 to 2.3	_	$0.2 \times V_{CC}$	v
H-level	H-level	Vон	$V_{OH}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OH</sub> = -100 μA	1.8	V <sub>CC</sub> - 0.2	_	
Output voltage		0.11		I <sub>OH</sub> = -4 mA	1.8	1.4	_	V
	L-level	Mai	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 100 μA	1.8	_	0.2	
	L-level V <sub>OL</sub>	VOL		I <sub>OL</sub> = 4 mA	1.8	_	0.3	
Input leakage curren	nt	I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V		1.8	—	±5.0	μA
3-state output OFF state current		I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		1.8		±10.0	μA
Power-off leakage c	urrent	I <sub>OFF</sub>	$V_{IN}$ , $V_{OUT} = 0$ to 3.6 V		0	_	10.0	μA
Quiescent supply cu	urrent		$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	
Quescent Supply Ct		Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	_	±20.0	μA

# AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ $\Omega$ ) (Note 1)

Characteristics	Symbol	Symbol Test Condition		Min		Unit
Characteristics	Symbol		V <sub>CC</sub> (V)	IVIIII	Max	Unit
Propagation delay time	tuu		1.8	1.5	5.8	
(D-Q)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5\pm0.2$	1.0	4.5	ns
(D-Q)	t <sub>pHL</sub>		$\textbf{3.3}\pm\textbf{0.3}$	0.8	3.3	
Dranagation dalay time	•		1.8	1.5	6.2	
Propagation delay time (LE-Q)	t <sub>pLH</sub> t	Figure 1, Figure 2	$2.5\pm0.2$	1.0	4.9	ns
	t <sub>pHL</sub>		$3.3\pm 0.3$	0.8	3.6	
			1.8	1.5	7.6	
3-state output enable time	t <sub>pZL</sub>	Figure 1, Figure 3	$2.5\pm0.2$	1.0	5.4	ns
	t <sub>pZH</sub>		$3.3\pm 0.3$	0.8	3.9	
		Figure 1, Figure 3	1.8	1.5	5.3	ns
3-state output disable time	t <sub>pLZ</sub>		$2.5\pm0.2$	1.0	4.4	
	t <sub>pHZ</sub>		$3.3\pm 0.3$	0.8	4.0	
		Figure 1, Figure 2	1.8	3.0	_	ns
Minimum pulse width	t <sub>w (H)</sub>		$2.5\pm0.2$	1.5	_	
(LE)			$3.3\pm 0.3$	1.5	_	
			1.8	2.5	_	
Minimum setup time	ts	Figure 1, Figure 2	$2.5\pm0.2$	1.5	_	ns
			$3.3\pm 0.3$	1.5	_	
			1.8	1.0	_	
Minimum hold time	t <sub>h</sub>	Figure 1, Figure 2	$2.5\pm0.2$	1.0	_	ns
			$3.3\pm 0.3$	1.0	_	
			1.8	_	0.5	
Output to output skew	t <sub>osLH</sub>	(Note 2)	$2.5\pm0.2$	_	0.5	ns
	t <sub>osHL</sub>		$3.3\pm 0.3$		0.5	

Note 1: For  $C_L = 50 \text{ pF}$ , add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.  $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, \ t_{osHL} = |t_{pHLm} - t_{pHLn}|)$ 

# Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 2.0 \text{ ns}$ , $C_L = 30 \text{ pF}$ )

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Symbol			$V_{CC}(V)$	тур.	Onit
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	0.15	
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	0.35	
	V <sub>OLV</sub>	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	-0.15	v
Quiet output minimum dynamic V <sub>OI</sub>		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	-0.25	
, 02		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	-0.35	
	V <sub>OHV</sub>	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	1.55	
Quiet output minimum dynamic V <sub>OH</sub>		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	2.65	

Note: Parameter guaranteed by design.

#### **Capacitive Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition		Тур.	Unit
			V <sub>CC</sub> (V)		
Input capacitance	C <sub>IN</sub>	—	1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C <sub>PD</sub>	f <sub>IN</sub> = 10 MHz (Note	) 1.8, 2.5, 3.3	20	pF

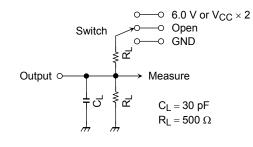
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16$  (per bit)

# TOSHIBA

## **AC Test Circuit**



Parameter	Switch		
t <sub>pLH</sub> , t <sub>pHL</sub>	Open		
t <sub>pLZ</sub> , t <sub>pZL</sub>			
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND		

Figure 1

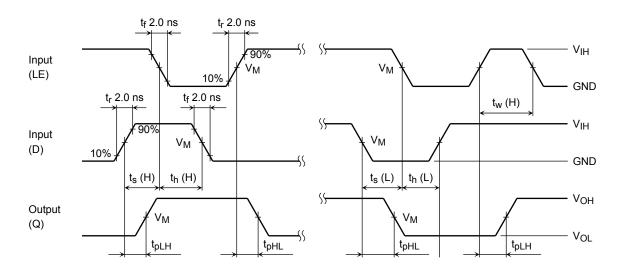
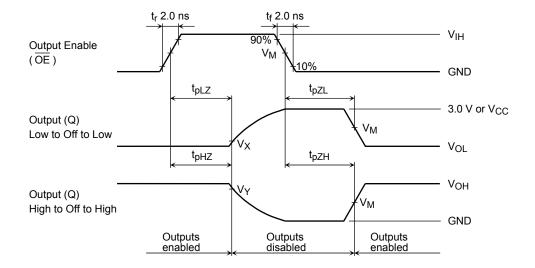


Figure 2  $t_{pLH}, t_{pHL}, t_w, t_s, t_h$ 

## AC Waveform

# TOSHIBA



Symbol	V <sub>CC</sub>				
Symbol	$3.3\pm0.3~V$	$2.5\pm0.2~V$	1.8 V		
VIH	2.7 V	V <sub>CC</sub>	V <sub>CC</sub>		
VM	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2		
VX	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V	V <sub>OL</sub> + 0.15 V		
Vy	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.15 V	V <sub>OH</sub> – 0.15 V		

# Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

# **TOSHIBA**

Unit: mm

# Package Dimensions

TSSOP48-P-0061-0.50A

48 6.1±0.1 8.1±0.2 24  $0.2^{+0.07}_{-0.06}$ 0.5 0.5TYP **⊕**0.1M 12.8MAX  $12.5 \pm 0.1$ 1.2MAX ᠳᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆᡆ  $1.0\pm0.05$ 0.1±0.05 0.125 +0.03 0~10° 0.25 (0.5) 0.45~0.75

Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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